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Rev. 04/03

Docket No. ELM-1 Cont. 13

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy

Application No.: 10/724,282 Confirmation No.: 5846

Filed: December 19, 2003

For : MEMBRANE 3D IC FABRICATION

Group Art Unit : 2814

Examiner : Not yet assigned

New York, New York

July 16, 2004

Hon. Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

# TRANSMITTAL LETTER FOR INFORMATION DISCLOSURE STATEMENT

Sir:

Transmitted herewith is an Information Disclosure

Statement in the above-identified application. This

Statement is submitted:

- [] within three months of the application filing date;
- [X] more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97, submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this

Information Disclosure Statement to Deposit Account No. 06-1075. A duplicate copy of this letter is transmitted herewith.

Respectfully submitted,

Philip R. Poh

Registration No. 51,176

Agent for Applicants

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I hereby certify that this Correspondence is being deposited with the U.S. Postal Service as First

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Commissioner for Patents

P.O. Box 1450

Alexandrian VA 22313-1450 on

Signature of Person Signing

### ELM-1 Cont.13



### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy

Application No.: 10/724,282 Confirmation No.: 5846

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Group Art Unit : 2814

Examiner : Not yet assigned

Hon. Commissioner for Patents

P.O. Box 1450

Alexandrian, Virginia 22313-1450

### INFORMATION DISCLOSURE STATEMENT

### Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97, applicant wishes to call the attention of the Examiner to the following documents:

### **U.S.** Patents

Fujii et al.	Re. 34,893	04/04/95
Foster	2,915,722	12/01/59
Farrand	3,202,948	08/24/65
Lesk	3,559,282	02/02/71
Burkhardt	3,560,364	02/02/71
Emmasingel	3,602,982	09/07/71
Medicus	3,615,901	10/26/71
Napoli et al.	3,716,429	02/13/73
Krishna et al.	3,777,227	12/14/73
Kuipers	3,868,565	02/25/75
Yerman	3,922,705	11/25/75
Wanlass	3,997,381	12/14/76
Stein	4,070,230	01/24/78
Greenwood et al.	4,131,985	01/02/79
Hauser, Jr., et al.	4,142,004	02/27/79
Hoeberechts	4,251,909	02/24/81

Kubacki	4,262,631	04/21/81
Shioya et al.	4,394,401	07/19/83
Trenkler et al.	4,401,986	08/30/83
Thomas et al.	4,416,054	11/22/83
Takagi et al.	4,539,068	09/03/85
Reid et al.	4,585,991	04/29/86
Yasumoto et al.	4,612,083	09/16/86
Belanger et al.	4,617,160	10/14/86
Shimizu et al.	4,618,397	10/21/86
Schmitz	4,618,763	10/21/86
Christensen	4,663,559	05/05/87
Burns et al.	4,684,436	08/04/87
Hatada	4,693,770	09/15/87
Maeda et al.	4,702,336	10/27/87
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Go	4,706,166	11/10/87
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Freeman	4,810,673	03/07/89
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Leedy	4,924,589	05/15/90
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Rokos	4,954,865	09/04/90
Shinomiya	4,957,882	09/18/90
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Mauger	4,966,663	10/30/90
Leedy	4,994,735	02/19/91
Keogh et al.	5,008,619	04/16/91
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Leedy	5,020,219	06/04/91
Leedy	5,034,685	07/23/91
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Findler et al.	5,071,510	12/10/91
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Leedy	5,103,557	04/14/92
Mauger	5,110,373	05/05/92
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Chan et al.	5,116,777	05/26/92
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Leedy	5,225,771	07/06/93
Bower et al.	5,236,118	08/17/93
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Leedy	5,323,035	06/21/94
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Leedy	5,354,695	10/11/94
MacDonald	5,363,021	11/08/94
Goossen	5,385,632	01/31/95
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Shimoji	5,420,458	05/30/95
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Toshiaki et al.	5,555,212	09/10/96
Ramm et al.	5,563,084	10/08/96
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Leedy	5,571,741	11/05/96
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Pierrat	5,582,939	12/10/96
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Leedy	5,592,007	01/07/97
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Val	5,637,536	06/10/97
var	5,057,550	00/10/3/

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Leedy	5,840,593	11/24/98
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Sotokawa et al.	5,868,949	02/09/99
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Sweatt et al.	5,870,176	02/09/99
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Leedy	5,946,559	08/31/99
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Cutter et al.	5,998,069	12/07/99
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Hendricks, et al., "Polyquinoline Coatings and Films: Improved Organic Dielectrics for IC's and MCM's," Eleventh IEEE/CHMT International Electronics Manufacturing Technology Symposium, pp. 361-265 (1991).

Knolle, W.R., et al., "Characterization of Oxygen-Doped, Plasma-Deposited Silicon Nitride," Journal of the Electrochemical Society, Vol. 135, No. 5, pp. 1211-1217, (May 1988).

Nguyen, S.V., "Plasma Assisted Chemical Vapor Deposited Thin Films for Microelectronic Applications, J. Vac. Sci. Technol. Vol. B4, No. 5, pp.1159-1167, (Sep/Oct. 1986).

Olmer, et al., "Intermetal Dielectric Deposition by Plasma Enhanced Chemical Vapor Deposition," Fifth IEEE/CHMT International Electronic Manufacturing Technology Symposium - Design-to-Manufacturing Transfer Cycle," pp. 98-99 (1988).

Runyan, W.R., "Deposition of Inorganic Thin Films," Semiconductor Integrated Circuit Processing Technology, p. 142 (1990).

Sze, S.M., "Surface Micromachining," Semiconductor Sensors, pp. 58-63 (1994).

Vossen, John L., "Plasma-Enhanced Chemical Vapor Deposition," Thin Film Processes II, pp. 536-541 (1991).

Wolf, Stanley, "Basic of Thin Films," Silicon Processing for the VLSI Era, pp. 115, 192-193 and 199 (1986).

Copies of the aforementioned documents are listed on the accompanying Form PTO-1449 (submitted in duplicate).

It is respectfully requested that these documents be: (1) fully considered by the Patent and Trademark Office during the examination of this application; and (2) printed on any patent which may issue on this application. Applicant requests that a copy of Form PTO-1449, as considered and initialized by the Examiner, be returned with the next communication.

Consideration of the foregoing in relation to this patent application is respectfully requested.

Respectfully submitted,

I hereby certify that this Correspondence is being deposited with the U.S.

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Addressed to:

Commissioner for Patents

P.O. Box 1450

Claire J. Saintil

Alexandria, VA 22313-1450 on

of Person Signing

Philip R. Poh

Registration No. 51,176

Agent for Applicant

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Tel.: (212) 596-9000

FORM PTO-1449

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## U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO. ELM-1 Cont. 13	APPLICATION NO. 10/724,282
APPLICANT Glenn J. Leedy	CONFIRMATION NO. 5846
FILING DATE December 19, 2003	GROUP 2814

**U.S. PATENT DOCUMENTS** 

EXAMINE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	Re. 34,893	04/04/95	Fujii et al.	257	419	
	2,915,722	12/01/59	Foster	336	115	
	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	
	3,602,982	09/07/71	Emmasingel	29	577	
	3,615,901	10/26/71	Medicus	148	11.5 R	
	3,716,429	02/13/73	Napoli et al.	156	17	
	3,777,227	12/14/73	Krishna et al.	257	578	
	3,868,565	02/25/75	Kuipers	324	207.26	
	3,922,705	11/25/75	Yerman	357	26	
	3,997,381	12/14/76	Wanlass	156	3	
	4,070,230	01/24/78	Stein	156	657	
	4,131,985	01/02/79	Greenwood et al.	29	580	
	4,142,004	02/27/79	Hauser, Jr. et al.	438	792	
	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	
	4,401,986	08/30/83	Trenkler et al.	340	870.32	
•	4,416,054	11/22/83	Thomas et al.	29	572	-
	4,539,068	09/03/85	Takagi et al.	156	614	
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	
	4,684,436	08/04/87	Burns et al.	216	65	
	4,693,770	09/15/87	Hatada	156	151	

**EXAMINER** 

FORM PTO-1449			OF COMMERCE DEMARK OFFICE	ATTY. DOCI ELM-1 Cont.		APPLICATION NO. 10/724,282	
	FORMATION TATEMENT B			APPLICANT Glenn J. Leedy		CONFIRMATION NO. 5846	
<u></u>	OTATEMENT D.		ANI	FILING DAT December 19		GROUP 2814	
		<u> </u>					
4,702,3	336	0/27/87	Maeda et al.	180	197		
4,702,9		0/27/87	Seibert et al.	427	583		
4,706,		1/10/87	Go	361	403		
4,721,9		1/26/88	Stevenson	338	4		
4,761,0		8/02/88	Reid	357	68		
4,784,		1/15/88	Holmen et al.	156	647		
4,810,0	673 0	3/07/89	Freeman	438	386		
4,825,		4/25/89	Mattox et al.	257	639		
4,857,4		8/15/89	Tam et al.	438	619		
4,924,	589 0	5/15/90	Leedy	438	6		
4,940,9	-	7/10/90	Borel et al.	313	306		
		1/26/96	Borel et al.	315	306		
4,950,9		8/21/90	Vranish et al.	324	207.23		
4,952,		8/18/90	Lee et al.	428	220		
4,954,		9/04/90	Rokos	257	378		
4,957,	1	9/18/90	Shinomiya	438	65		
4,965,4		0/23/90	Young et al.	200	83 N		
4,966,0	663 1	0/30/90	Mauger	205	656		
4,994,	735 0	2/19/91	Leedy	324	158_		
5,008,0	619 0	4/16/91	Keogh et al.	324	207.17		
5,010,0	024 0	4/23/91	Allen et al.	438	659		
5,020,	219 0	6/04/91	Leedy	29	846		
5,034,0	685 0	7/23/91	Leedy	324	158 F		
5,070,		2/03/91	Greenwald et al.	437	3		
5,071,	i	2/10/91	Findler et al.	156	647		
5,098,		3/24/92	Machado et al.	438	788		
5,103,	1	4/14/92	Leedy	29	832		
5,110,		5/05/92	Mauger	148	33.2		
5,111,		5/05/92	Eichelberger	357	75		
5,116,		5/26/92	Chan et al.	438	234		
5,130,	1 -	7/14/92	Miller	361	393		
5,132,		7/21/92	Roy	438	477		

FORM PTO-1449	ENT OF COMMERCE RADEMARK OFFICE		ATTY. DOC ELM-1 Cont		APPLICATION NO. 10/724,282	
	FORMATION DISC		I .	APPLICANT Glenn J. Lee		CONFIRMATION NO 5846
J	TATEMENT BY ALL	LIOANI	1 '	ILING DAT December 1		GROUP 2814
5,151,	775 09/29/9	2 Hadwin		357	80	
5,156,	909 10/20/9	2 Henager, Jr. et a	l.	428	334	
5,203,	731 04/20/9	3 Zimmerman		445	24	
5,225,	771 07/06/9	3 Leedy		324	158	
5,236,	118 08/17/9	3 Bower et al.		228	193	
5,262,	351 11/16/9	3 Bureau et al.		437	183	
5,270,	261 12/14/9	3 Bertin et al.		437	209	
5,273,	940 12/28/9	3 Sanders		437	209	
5,274,	270 12/28/9	3 Tuckerman		257	758	
5,279,	865 01/18/9	4 Chebi et al.		427	574	
5,284,	796 02/08/9	4 Nakanishi et al.		437	183	•
5,323,	035 06/21/9	4 Leedy		257	48	
5,324,	687 06/28/9	4 Wojnarowski		437	225	
5,354,	695 10/11/9	4 Leedy		438	411	
5,363,	021 11/08/9	4 MacDonald		315	366	
5,385,	909 01/31/9	5 Nelson et al.		514	291	
5,385,	632 01/31/9	5 Goossen		156	630	
5,420,	458 05/30/9	5 Shimoji		257	622	
5,424,	920 06/13/9	5 Miyake		361	735	
5,426,	072 06/20/9	5 Finnila		437	208	
5,426,	363 06/20/9	5 Akagi et al.		324	239	
5,432,	444 07/11/9	5 Yasohama et al.		324	240	
5,432,				365	63	
5,434,				324	67	
5,451,				430	313	
5,453,		<u> </u>		437	203	
5,457,		1		29	895	
5,476,				437	132	
5,489,				437	208	
5,502,0				365	51	
5,512,	i	· · · · · · · · · · · · · · · · · · ·		430	30	
5,527,0				430	5	

FORM PTO-1449		NT OF COMMERCE RADEMARK OFFICE	ATTY. DOCI		. APPLICATION NO. 10/724,282	
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OTATE OF ALL PROPERTY OF ALL P		LICANT	FILING DAT December 1		GROUP 2814	
5,529	829 06/25/9	6 Koskenmaki et al.	428	167		
5,534		Frye et al.	437	209		
5,555	,212 09/10/9	Toshiaki et al.	365	200		
5,563		Ramm et al.	437	51		
5,571	741 11/05/9	6 Leedy	437	51		
5,580	,687 12/03/9	6 Leedy	430	5		
5,581	•	<del></del>	365	63		
5,582			430	5		
5,583	,688 12/10/9	6 Hornbeck	359	291		
5,592	,007 01/07/9	7 Leedy	257	347		
5,592	,018 01/07/9	7 Leedy	257	619		
5,595	,933 01/21/9	7 Heijboer	439	20		
5,606	,186 02/25/9	7 Noda	257	226		
5,627	,112 05/06/9	7 Tennant et al.	438	113		
5,629	,137 05/13/9	7 Leedy	430	313		
5,633	,209 05/27/9	7 Leedy	435	228		
5,637	,536 06/10/9	7 Val	438	686		
5,654	,127 08/05/9	7 Leedy	430	315		
5,654	,220 08/05/9	7 Leedy	438	25		
5,656	,552 08/12/9	7 Hudak et al.	438	15		
5,675	,185 10/07/9	7 Chen et al.	257	774		
5,694	,588 12/02/9	7 Ohara et al.	395	566		
5,725	,995 03/10/9	8 Leedy	430	315		
5,750	,211 05/12/9	8 Weise et al.	427	579		
5,760	,478 06/02/9	Bozso et al.	257	777		
5,773	,152 06/30/9	8 Okonogi	428	446		
5,786	,116 07/28/9	8 Rolfson	430	5		
5,793	,115 08/11/9	8 Zavracky et al.	257	777		
5,831	,280 11/03/9	8 Ray	257	48		
5,834	,334 11/10/9	8 Leedy	438	107		
5,840	,593 11/24/9	8 Leedy	438	6		
5,856	,695 01/05/9	9 Ito et al.	257	370		

FORM PTO-1	FORM PTO-1449 U.S. DEPART PATENT AND					ATTY. DOO ELM-1 Con		APPLICATIO 10/724,282	N NO.
	INFORMATIO		CLOSURE PPLICANT			APPLICANT Glenn J. Leedy		CONFIRMAT 5846	TION NO.
	STATEMENT	DIAP				FILING DA December		GROUP 2814	
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	5,868,949	02/09/	99	Sotokaw	a et al.	216	18		
	5,869,354	02/09/	99	Leedy		438	110		
	5,870,176	02/09/	99	Sweatt e	t al.	355	53		
	5,880,010	03/09/	99	Davidsor	n	438	455		
	5,882,532	03/16/	99	Field et a	al.	216	2		
	5,902,118	05/11/	99	Hübner		438	106		
	5,915,167	06/22/	99	Leedy		438	108		
	5,946,559 08/3		99	Leedy		438	157		
	5,985,693	11/16/	99	Leedy		438	107		
	5,998,069	12/07/	99			430	5		
	6,008,126	12/28/	99			438	667		
	6,020,257	02/01/	00			438	626		
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